

**Amendments to the Specification:**

Page 1, Paragraph 1, please amend the title as follows:

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE—AND  
FABRICATING METHOD THEREOF

# SEMICONDUCTOR DEVICE AND

## FABRICATING METHOD THEREOF

*This application is a DIV of 10/214,693 08/09/02 which is a  
DIV of 09/120,244 07/22/1998 PAT 6,432,756.*

### BACKGROUND OF THE INVENTION

#### 5 1. Field of the Invention:

The present invention disclosed in the specification relates to a method of fabricating a thin film transistor using a crystalline semiconductor film.

#### 2. Description of Related Art:

10 Conventionally, there has been known a thin film transistor (hereinafter, referred to as TFT) using an amorphous silicon film. The transistor is utilized mainly for constituting an active matrix circuit of a liquid crystal display device of an active matrix type.

However, according to TFT using an amorphous silicon film,  
15 there poses a problem where the operational speed is retarded and a P-channel type one cannot be reduced to practice.

The transistor cannot be used in a liquid crystal display device of an active matrix type integrated with a peripheral drive circuit and various integrated circuits cannot be constituted by  
20 using such TFT because of such a problem.

There has been known a constitution using a crystalline silicon film as means for resolving the problem.

As methods of fabricating a crystalline silicon film, there are classified roughly into a method by heating and a method by  
25 irradiation of laser beam.

According to the method by heating, there poses a problem where a glass substrate cannot be utilized since a process at a high temperature as high as 900 °C or higher is needed.

In consideration of the fact that a major field of application of  
30 TFT is a liquid crystal display device, capability of utilizing a glass substrate as a substrate constitutes a problem with priority.